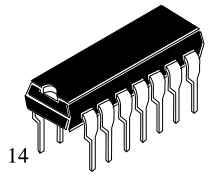
IW4069UB

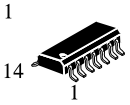
Hex Inverter
High-Voltage Silicon-Gate CMOS

The IW4069UB types consist of six inverter circuits. These devices are intended for all general-purpose inverter applications where the medium-power TTL-drive and logic-level-conversion capabilities of circuits such as the IW4049UB Hex Inverter/Buffers are not required. Each of the six inverters is a single stage

- Operating Voltage Range: 3.0 to 18 V
- Maximum input current of 1 μA at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- Noise margin (over full package temperature range):
  0.5 V min @ 5.0 V supply
  1.0 V min @ 10.0 V supply
  1.5 V min @ 15.0 V supply



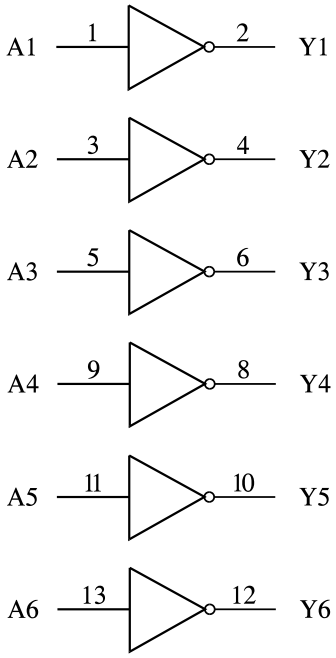
N SUFFIX
PLASTIC



D SUFFIX
SOIC

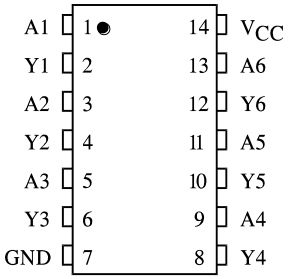
ORDERING INFORMATION
IW4069UBN Plastic
IW4069UBD SOIC
T_A = -55° to 125° C for all packages

LOGIC DIAGRAM



PIN 14 =V_{CC}
PIN 7 = GND

PIN ASSIGNMENT



FUNCTION TABLE

Inputs	Output
A	Y
L	H
H	L

L – LOW voltage level

H – HIGH voltage level

ABSOLUTE MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	-0.5 to +20	V
V_{IN}	DC Input Voltage (Referenced to GND)	-0.5 to V_{CC} +0.5	V
I_{IN}	DC Input Current, per Pin	±10	mA
P_D	Power Dissipation in Still Air, Plastic DIP+ SOIC Package+	500 500	mW
Ptot	Power Dissipation per Output Transistor	100	mW
Tstg	Storage Temperature	-65 to +150	°C

*Maximum Ratings are those values beyond which damage to the device may occur.
Functional operation should be restricted to the Recommended Operating Conditions.
+Derating - Plastic DIP: - 12 mW/°C from 100° to 125°C
SOIC Package: : - 7 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	3.0	18	V
V_{IN}, V_{OUT}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V_{CC}	V
T_A	Operating Temperature, All Package Types	-55	+125	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{IN} and V_{OUT} should be constrained to the range GND≤(V_{IN} or V_{OUT})≤V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V_{CC} V	Guaranteed Limit			Unit
				≥-55°C	25°C	≤125 °C	
V_{IH}	Minimum High-Level Input Voltage	V_{OUT}=0.5V V_{OUT}=1.0 V V_{OUT}=1.5V	5.0 10 15	4.0 8.0 12.5	4.0 8.0 12.5	4.0 8.0 12.5	V
V_{IL}	Maximum Low -Level Input Voltage	V_{OUT}= V_{CC} - 0.5 V V_{OUT}= V_{CC} - 1 V V_{OUT}= V_{CC} - 1.5 V	5.0 10 15	1.0 2.0 2.5	1.0 2.0 2.5	1.0 2.0 2.5	V
V_{OH}	Minimum High-Level Output Voltage	V_{IN}=GND	5.0 10 15	4.95 9.95 14.95	4.95 9.95 14.95	4.95 9.95 14.95	V
V_{OL}	Maximum Low-Level Output Voltage	V_{IN}= V_{CC}	5.0 10 15	0.05 0.05 0.05	0.05 0.05 0.05	0.05 0.05 0.05	V
I_{IN}	Maximum Input Leakage Current	V_{IN}= GND or V_{CC}	18	±0.1	±0.1	±1.0	μA
I_{CC}	Maximum Quiescent Supply Current (per Package)	V_{IN}= GND or V_{CC}	5.0 10 15 20	0.25 0.5 1.0 5.0	0.25 0.5 1.0 5.0	7.5 15 30 150	μA
I_{OL}	Minimum Output Low (Sink) Current	V_{IN}= GND or V_{CC} U_{OL}=0.4 V U_{OL}=0.5 V U_{OL}=1.5 V	 5.0 10 15	 0.64 1.6 4.2	 0.51 1.3 3.4	 0.36 0.9 2.4	mA
I_{OH}	Minimum Output High (Source) Current	V_{IN}= GND or V_{CC} U_{OH}=2.5 V U_{OH}=4.6 V U_{OH}=9.5 V U_{OH}=13.5 V	 5.0 5.0 10 15	 -2.0 -0.64 -1.6 -4.2	 -1.6 -0.51 -1.3 -3.4	 -1.15 -0.36 -0.9 -2.4	mA

AC ELECTRICAL CHARACTERISTICS (C_L=50pF, R_L=200kΩ, Input t_r=t_f=20 ns)

Symbol	Parameter	V_{CC} V	Guaranteed Limit ≥-55°C	Guaranteed Limit 25°C	Guaranteed Limit ≤125°C	Unit
t_{PLH}, t_{PHL}	Maximum Propagation Delay, Input A to Output Y (Figure 1)	5.0 10 15	110 60 50	110 60 50	110 80 80	ns
t_{TLH}, t_{THL}	Maximum Output Transition Time, Any Output (Figure 1)	5.0 10 15	200 100 80	200 100 80	200 100 80	ns
C_{IN}	Maximum Input Capacitance	-		15		pF

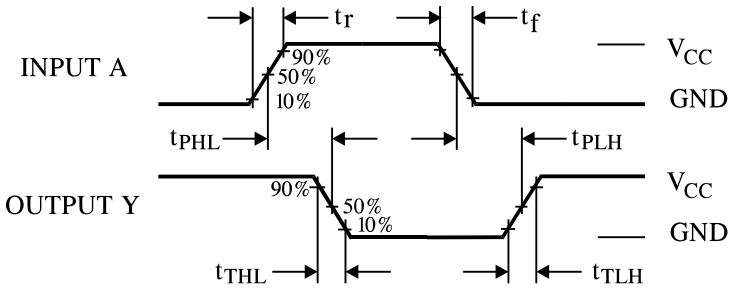
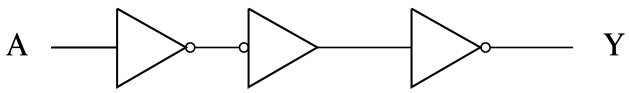
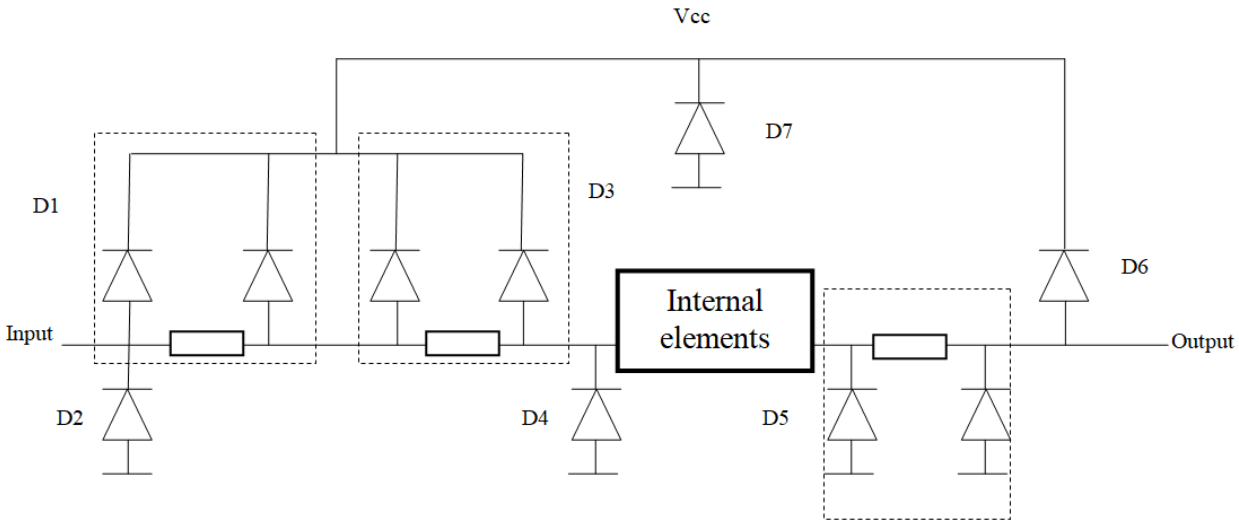


Figure 1. Switching Waveforms

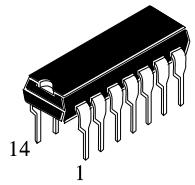
EXPANDED LOGIC DIAGRAM
(1/6 of the Device)

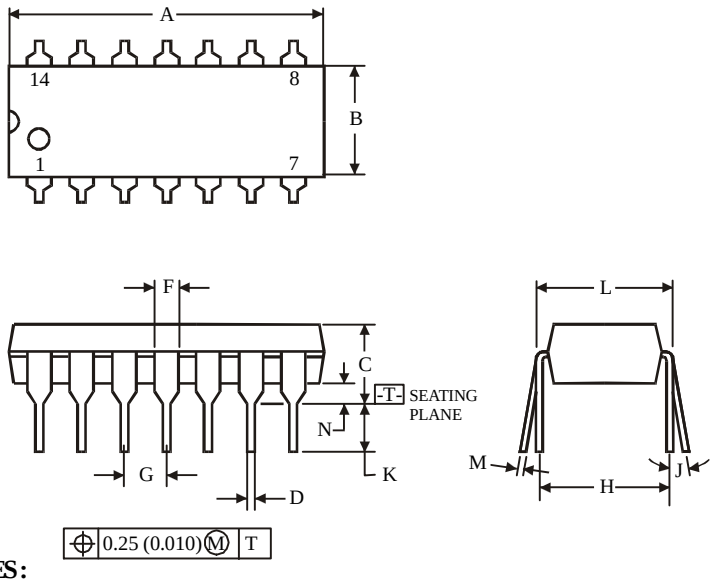


INPUT/OUTPUT PROTECTION CIRCUIT
(for each element)



N SUFFIX PLASTIC DIP
(MS - 001AA)



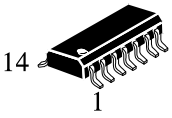


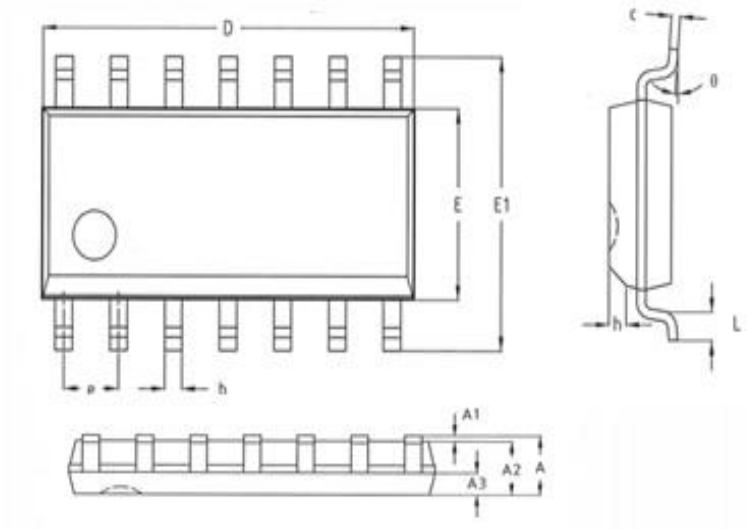
	Dimension, mm	
Symbol	**MIN**	**MAX**
A	18.67	19.69
B	6.1	7.11
C		5.33
D	0.36	0.56
F	1.14	1.78
G	2.54	
H	7.62	
J	0°	10°
K	2.92	3.81
L	7.62	8.26
M	0.2	0.36
N	0.38	

NOTES:

1. Dimensions “A”, “B” do not include mold flash or protrusions.
   Maximum mold flash or protrusions 0.25 mm (0.010) per side.

D SUFFIX SOIC
(MS - 012AB)





Symbol	min	avg	max
A			1.75
A1	0.05		0.09
A2	1.35	1.45	1.55
A3	0.60	0.65	0.70
b	0.35		0.50
c	0.19		0.25
D	8.50	8.60	8.70
E	3.80	3.90	4.00
E1	5.80	6.00	6.20
e	1.27BSC		
h	0.30		0.50
L	0.40		0.80
Θ	0.00		8.00

UNIT: mm